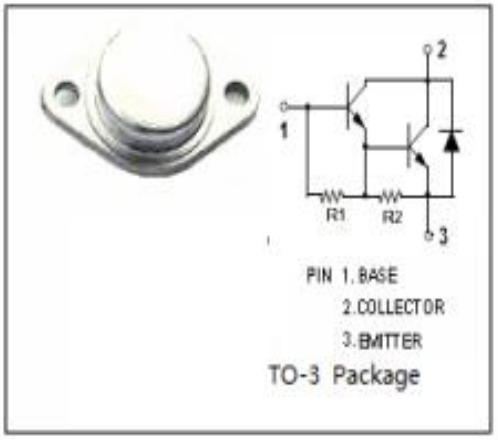
isc Silicon NPN Darlington Power Transistor MJ4034

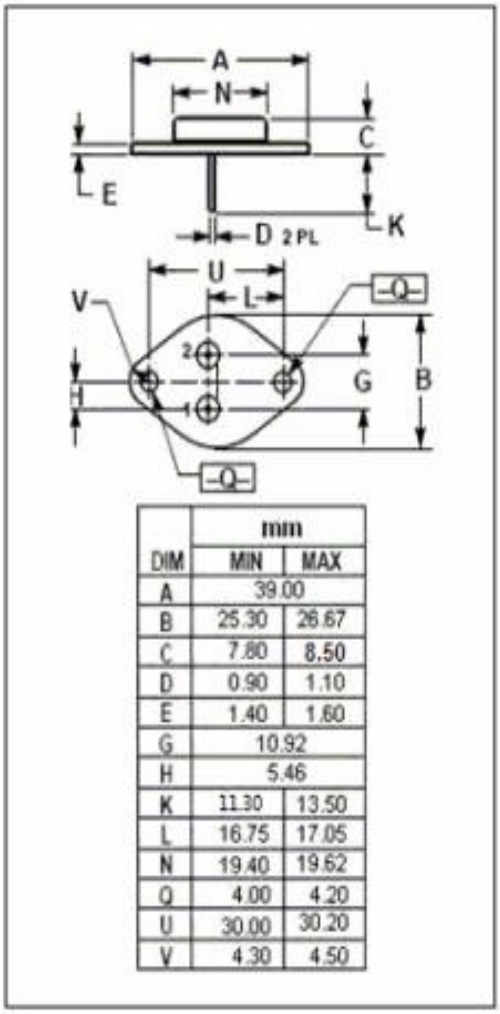
DESCRIPTION

- With TO-3 packaging
- Very high DC current gain
- Monolithic darlington transistor with integrated antiparallel collector-emitter diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Electronic ignition
- Alternator regulator
- Motor controls



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Max.Collector Current-Continuous	20	A
I_B	Base Current- Continuous	0.5	A
P_D	Collector Power Dissipation	150	W
T_j	Max.Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.17	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA, I_B= 0	80		V
$V_{CE(sat)1}$	Collector-Emitter Saturation Voltage	I_C= 10A ,I_B=40mA		2.5	V
$V_{CE(sat)2}$	Collector-Emitter Saturation Voltage	I_C= 16A ,I_B= 80mA		4.0	V
$V_{BE(on)}$	Base-Emitter Saturation Voltage	I_C= 10A ,V_{CE}= 3.0V		3.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 40V, I_B= 0		3.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		5.0	mA
h_{FE-1}	DC Current Gain	I_C= 10A ; V_{CE}=3V	1000		